



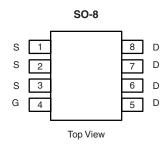
P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
	0.011 at V _{GS} = - 10 V	- 13.7			
- 20	0.014 at V _{GS} = - 4.5 V	- 12.3			
	0.020 at V _{GS} = - 2.5 V	- 10.3			

FEATURES

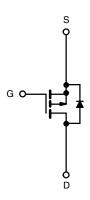
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs





Ordering Information: Si4463BDY-T1-E3 (Lead (Pb)-free)

Si4463BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	_A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Dunis Comment /T 150 90\8	T _A = 25 °C	- I _D	- 13.7	- 9.8	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 11.1	- 7.9	
Pulsed Drain Current		I _{DM}	- 50		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.7	- 1.36	1
M	T _A = 25 °C	D.	3.0	1.5	W
Maximum Power Dissipation ^a	T _A = 70 °C	- P _D	1.9	0.95	l vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum boration to Ambienta	t ≤ 10 s	R_{thJA}	35	42		
Maximum Junction-to-Ambient ^a	Steady State	□thJA	70	84	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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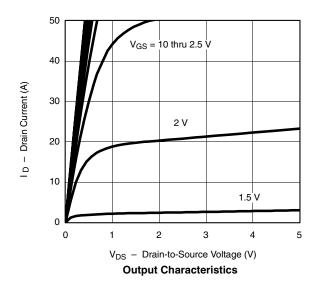
Parameter	Symbol	Test Conditions		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.6		- 1.4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μΑ	
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 70 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 30			Α	
	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 13.7 A	0.0085		0.011		
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 12.3 A		0.010	0.014 Ω		
		V _{GS} = - 2.5 V, I _D = - 5 A	V _{GS} = - 2.5 V, I _D = - 5 A 0.015 0.		0.020		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 13.7 A		44		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 2.7 A, V _{GS} = 0 V		- 0.7	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Qg			37	56		
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -13.7 \text{ A}$		8.7		nC	
Gate-Drain Charge	Q_{gd}			11			
Gate Resistance	R_g	f = 1 MHz		2.7		Ω	
Turn-On Delay Time	t _{d(on)}			35	55		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		60	90		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		115	170	ns	
Fall Time	t _f			75	115		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.3 A, dl/dt = 100 A/μs		50	75		

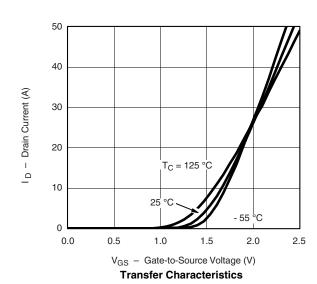
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



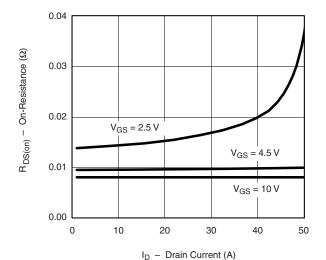




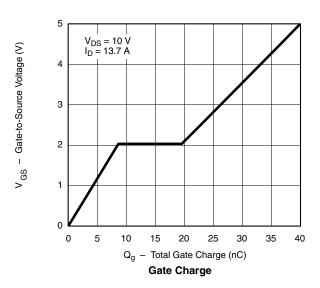


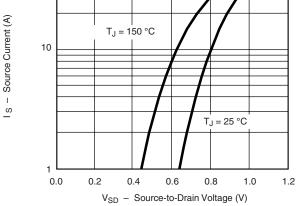


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

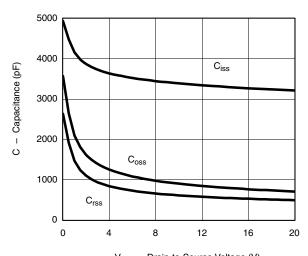


On-Resistance vs. Drain Current

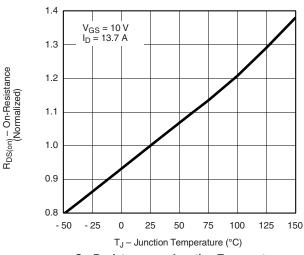




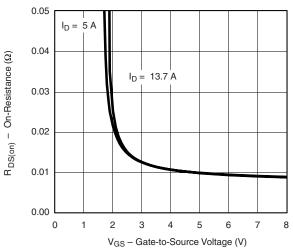
Source-Drain Diode Forward Voltage



V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



On-Resistance vs. Junction Temperature



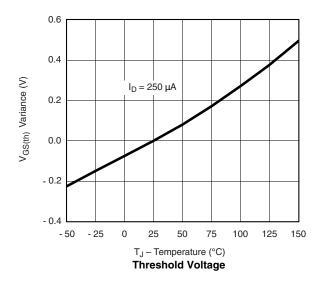
On-Resistance vs. Gate-to-Source Voltage

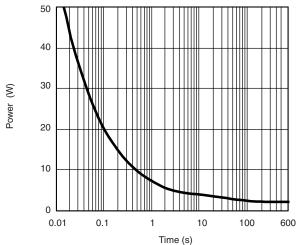
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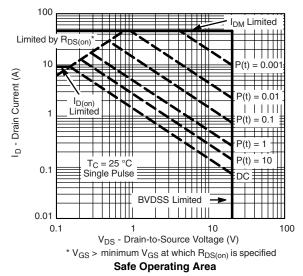
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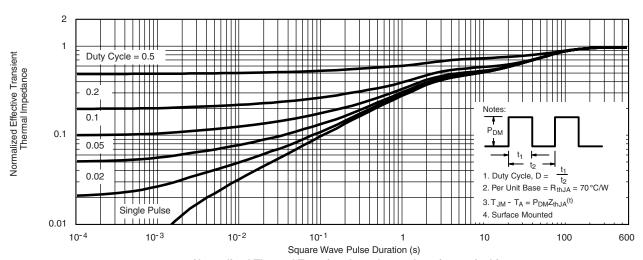
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Single Pulse Power, Junction-to-Ambient

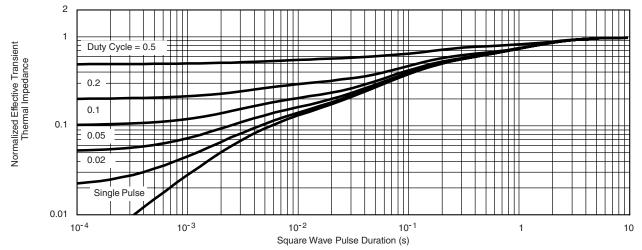




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIMETERS INCH			HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050) BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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